

1 Pin Assignments

This section includes diagrams of the MSC7116 package ball grid array layouts and pinout allocation tables.

1.1 MAP-BGA Ball Layout Diagrams

Top and bottom views of the MAP-BGA package are shown in **Figure 2** and **Figure 3** with their ball location index numbers.

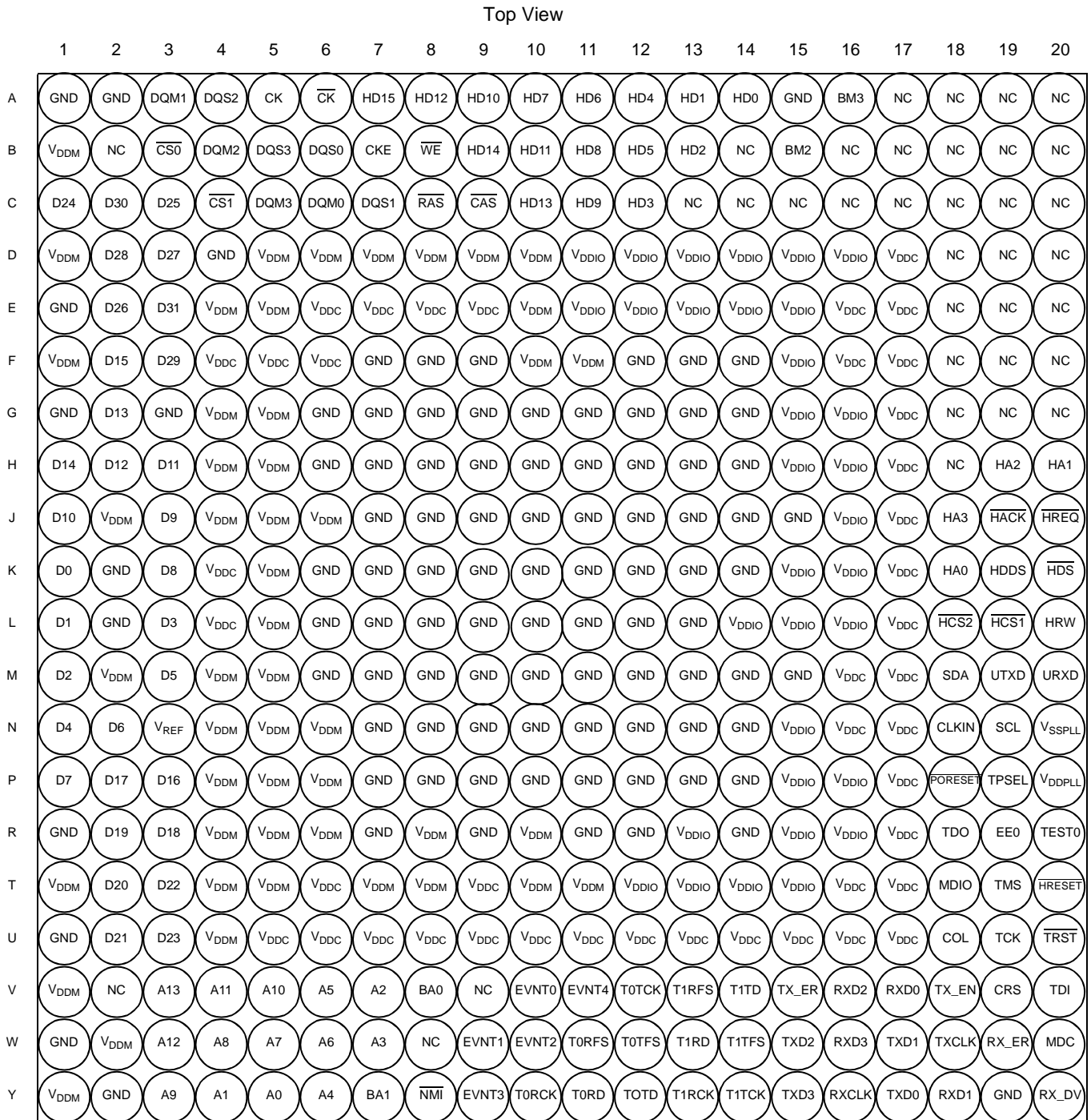


Figure 2. MSC7116 Molded Array Process-Ball Grid Array (MAP-BGA), Top View

Because of an order from the United States International Trade Commission, BGA-packaged product lines and part numbers indicated here currently are not available from Freescale for import or sale in the United States prior to September 2010: MSC7116VF1000, MSC7116VM1000, MSC7116XADS

Bottom View

	20	19	18	17	16	15	14	13	12	11	10	9	8	7	6	5	4	3	2	1	
A	NC	NC	NC	NC	BM3	GND	HD0	HD1	HD4	HD6	HD7	HD10	HD12	HD15	\overline{CK}	CK	DQS2	DQM1	GND	GND	
B	NC	NC	NC	NC	NC	BM2	NC	HD2	HD5	HD8	HD11	HD14	\overline{WE}	CKE	DQS0	DQS3	DQM2	$\overline{CS0}$	NC	V _{DDM}	
C	NC	NC	NC	NC	NC	NC	NC	NC	HD3	HD9	HD13	\overline{CAS}	\overline{RAS}	DQS1	DQM0	DQM3	$\overline{CS1}$	D25	D30	D24	
D	NC	NC	NC	V _{DD}	V _{DDIO}	V _{DDIO}	V _{DDIO}	V _{DDIO}	V _{DDIO}	V _{DDIO}	V _{DDIO}	V _{DDM}	V _{DDM}	V _{DDM}	V _{DDM}	V _{DDM}	V _{DDM}	GND	D27	D28	V _{DDM}
E	NC	NC	NC	V _{DD}	V _{DD}	V _{DDIO}	V _{DDIO}	V _{DDIO}	V _{DDIO}	V _{DDIO}	V _{DDM}	V _{DD}	V _{DD}	V _{DD}	V _{DD}	V _{DD}	V _{DDM}	V _{DDM}	D31	D26	GND
F	NC	NC	NC	V _{DD}	V _{DD}	V _{DDIO}	GND	GND	GND	V _{DDM}	V _{DDM}	GND	GND	GND	V _{DD}	V _{DD}	V _{DD}	D29	D15	V _{DDM}	
G	NC	NC	NC	V _{DD}	V _{DDIO}	V _{DDIO}	GND	GND	GND	GND	GND	GND	GND	GND	GND	V _{DDM}	V _{DDM}	GND	D13	GND	
H	HA1	HA2	NC	V _{DD}	V _{DDIO}	V _{DDIO}	GND	GND	GND	GND	GND	GND	GND	GND	GND	V _{DDM}	V _{DDM}	D11	D12	D14	
J	\overline{HREQ}	\overline{HACK}	HA3	V _{DD}	V _{DDIO}	GND	GND	GND	GND	GND	GND	GND	GND	GND	V _{DDM}	V _{DDM}	V _{DDM}	D9	V _{DDM}	D10	
K	\overline{HDS}	HDDS	HA0	V _{DD}	V _{DDIO}	V _{DDIO}	GND	GND	GND	GND	GND	GND	GND	GND	GND	V _{DDM}	V _{DD}	D8	GND	D0	
L	HRW	$\overline{HCS1}$	$\overline{HCS2}$	V _{DD}	V _{DDIO}	V _{DDIO}	V _{DDIO}	GND	GND	GND	GND	GND	GND	GND	GND	V _{DDM}	V _{DD}	D3	GND	D1	
M	URXD	UTXD	SDA	V _{DD}	V _{DD}	GND	GND	GND	GND	GND	GND	GND	GND	GND	GND	V _{DDM}	V _{DDM}	D5	V _{DDM}	D2	
N	V _{SSPLL}	SCL	CLKIN	V _{DD}	V _{DD}	V _{DDIO}	GND	GND	GND	GND	GND	GND	GND	GND	V _{DDM}	V _{DDM}	V _{DDM}	V _{REF}	D6	D4	
P	V _{DDPLL}	TPSEL	$\overline{PORESET}$	V _{DD}	V _{DDIO}	V _{DDIO}	GND	GND	GND	GND	GND	GND	GND	GND	V _{DDM}	V _{DDM}	V _{DDM}	D16	D17	D7	
R	TEST0	EE0	TDO	V _{DD}	V _{DDIO}	V _{DDIO}	GND	V _{DDIO}	GND	GND	V _{DDM}	GND	V _{DDM}	GND	V _{DDM}	V _{DDM}	V _{DDM}	D18	D19	GND	
T	\overline{HRESET}	TMS	MDIO	V _{DD}	V _{DD}	V _{DDIO}	V _{DDIO}	V _{DDIO}	V _{DDIO}	V _{DDM}	V _{DDM}	V _{DD}	V _{DDM}	V _{DDM}	V _{DD}	V _{DDM}	V _{DDM}	D22	D20	V _{DDM}	
U	\overline{TRST}	TCK	COL	V _{DD}	V _{DD}	V _{DD}	V _{DD}	V _{DD}	V _{DD}	V _{DD}	V _{DD}	V _{DD}	V _{DD}	V _{DD}	V _{DD}	V _{DD}	V _{DD}	V _{DDM}	D23	D21	GND
V	TDI	CRS	TX_EN	RXD0	RXD2	TX_ER	T1TD	T1RFS	T0TCK	EVNT4	EVNT0	NC	BA0	A2	A5	A10	A11	A13	NC	V _{DDM}	
W	MDC	RX_ER	TXCLK	TXD1	RXD3	TXD2	T1TFS	T1RD	T0TFS	T0RFS	EVNT2	EVNT1	NC	A3	A6	A7	A8	A12	V _{DDM}	GND	
Y	RX_DV	GND	RXD1	TXD0	RXCLK	TXD3	T1TCK	T1RCK	T0TD	T0RD	T0RCK	EVNT3	\overline{NMI}	BA1	A4	A0	A1	A9	GND	V _{DDM}	

Figure 3. MSC7116 Molded Array Process-Ball Grid Array (MAP-BGA), Bottom View

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Table 1. MSC7116 Signals by Ball Designator (continued)

Number	Signal Names					
	End of Reset	Software Controlled			Hardware Controlled	
		GPI Enabled (Default)	Interrupt Enabled	GPO Enabled	Primary	Alternate
B14						NC
B15	BM2		GPID7		GPOD7	reserved
B16						NC
B17						NC
B18						NC
B19						NC
B20						NC
C1						D24
C2						D30
C3						D25
C4						$\overline{CS1}$
C5						DQM3
C6						DQM0
C7						DQS1
C8						\overline{RAS}
C9						\overline{CAS}
C10			GPIC5		GPOC5	HD13
C11			GPIC1		GPOC1	HD9
C12			reserved			HD3
C13						NC
C14						NC
C15						NC
C16						NC
C17						NC
C18						NC
C19						NC
C20						NC
D1						V_{DDM}
D2						D28
D3						D27
D4						GND
D5						V_{DDM}
D6						V_{DDM}
D7						V_{DDM}
D8						V_{DDM}
D9						V_{DDM}

Table 1. MSC7116 Signals by Ball Designator (continued)

Number	Signal Names					
	End of Reset	Software Controlled			Hardware Controlled	
		GPI Enabled (Default)	Interrupt Enabled	GPO Enabled	Primary	Alternate
U2					D21	
U3					D23	
U4					V _{DDM}	
U5					V _{DDC}	
U6					V _{DDC}	
U7					V _{DDC}	
U8					V _{DDC}	
U9					V _{DDC}	
U10					V _{DDC}	
U11					V _{DDC}	
U12					V _{DDC}	
U13					V _{DDC}	
U14					V _{DDC}	
U15					V _{DDC}	
U16					V _{DDC}	
U17					V _{DDC}	
U18			reserved			COL
U19					TCK	
U20					$\overline{\text{TRST}}$	
V1					V _{DDM}	
V2					NC	
V3					A13	
V4					A11	
V5					A10	
V6					A5	
V7					A2	
V8					BA0	
V9					NC	
V10			reserved			EVNT0
V11	SWTE	GPIA16	$\overline{\text{IRQ12}}$	GPOA16		EVNT4
V12		GPIA8	$\overline{\text{IRQ6}}$	GPOA8		T0TCK
V13		GPIA4	$\overline{\text{IRQ1}}$	GPOA4		T1RFS
V14		GPIA0	$\overline{\text{IRQ11}}$	GPOA0		T1TD
V15		GPIA28	$\overline{\text{IRQ17}}$	GPOA28	TX_ER	reserved
V16		GPIA6		GPOD6	RXD2	reserved
V17		GPIA22	$\overline{\text{IRQ22}}$	GPOA22		RXD0

Table 1. MSC7116 Signals by Ball Designator (continued)

Number	Signal Names					
	End of Reset	Software Controlled			Hardware Controlled	
		GPI Enabled (Default)	Interrupt Enabled	GPO Enabled	Primary	Alternate
V18	GPIA24		$\overline{\text{IRQ}}_{24}$	GPOA24	TX_EN	
V19	reserved				CRS	
V20	TDI					
W1	GND					
W2	V_{DDM}					
W3	A12					
W4	A8					
W5	A7					
W6	A6					
W7	A3					
W8	NC					
W9	GPIA17		$\overline{\text{IRQ}}_{13}$	GPOA17	EVNT1	CLKO
W10	BM0	GPIC14		GPOC14	EVNT2	
W11	GPIA10		$\overline{\text{IRQ}}_{5}$	GPOA10	T0RFS	
W12	GPIA7		$\overline{\text{IRQ}}_{7}$	GPOA7	T0TFS	
W13	GPIA3		$\overline{\text{IRQ}}_{8}$	GPOA3	T1RD	
W14	GPIA1		$\overline{\text{IRQ}}_{10}$	GPOA1	T1TFS	
W15	GPID4			GPOD4	TXD2	reserved
W16	GPIA27		$\overline{\text{IRQ}}_{18}$	GPOA27	RXD3	reserved
W17	GPIA19		$\overline{\text{IRQ}}_{19}$	GPOA19	TXD1	
W18	GPIA23		$\overline{\text{IRQ}}_{23}$	GPOA23	TXCLK or REFCLK	
W19	GPIA26		$\overline{\text{IRQ}}_{26}$	GPOA26	RX_ER	
W20	H8BIT	reserved			MDC	
Y1	V_{DDM}					
Y2	GND					
Y3	A9					
Y4	A1					
Y5	A0					
Y6	A4					
Y7	BA1					
Y8	reserved		$\overline{\text{NMI}}$	reserved		
Y9	BM1	GPIC15		GPOC15	EVNT3	
Y10	GPIA11		$\overline{\text{IRQ}}_{4}$	GPOA11	T0RCK	
Y11	GPIA9			GPOA9	T0RD	
Y12	GPIA6			GPOA6	T0TD	
Y13	GPIA5		$\overline{\text{IRQ}}_{0}$	GPOA5	T1RCK	

Table 1. MSC7116 Signals by Ball Designator (continued)

Number	Signal Names					
	End of Reset	Software Controlled			Hardware Controlled	
		GPI Enabled (Default)	Interrupt Enabled	GPO Enabled	Primary	Alternate
Y14	GPIA2	$\overline{\text{IRQ9}}$	GPOA2	T1TCK		
Y15	GPIA29	$\overline{\text{IRQ16}}$	GPOA29	TXD3	reserved	
Y16	GPI D5		GPO D5	RXCLK	reserved	
Y17	GPIA20	$\overline{\text{IRQ20}}$	GPOA20	TXD0		
Y18	GPIA21	$\overline{\text{IRQ21}}$	GPOA21	RXD1		
Y19	GND					
Y20	GPIA25	$\overline{\text{IRQ25}}$	GPOA25	RX_DV or CRS_DV		

2 Electrical Characteristics

This document contains detailed information on power considerations, DC/AC electrical characteristics, and AC timing specifications. For additional information, see the *MSC711x Reference Manual*.

2.1 Maximum Ratings

CAUTION

This device contains circuitry protecting against damage due to high static voltage or electrical fields; however, normal precautions should be taken to avoid exceeding maximum voltage ratings. Reliability is enhanced if unused inputs are tied to an appropriate logic voltage level (for example, either GND or V_{DD}).

In calculating timing requirements, adding a maximum value of one specification to a minimum value of another specification does not yield a reasonable sum. A maximum specification is calculated using a worst case variation of process parameter values in one direction. The minimum specification is calculated using the worst case for the same parameters in the opposite direction. Therefore, a “maximum” value for a specification never occurs in the same device with a “minimum” value for another specification; adding a maximum to a minimum represents a condition that can never exist.

Electrical Characteristics

Table 2 describes the maximum electrical ratings for the MSC7116.

Table 2. Absolute Maximum Ratings

Rating	Symbol	Value	Unit
Core supply voltage	V_{DDC}	1.5	V
Memory supply voltage	V_{DDM}	4.0	V
PLL supply voltage	V_{DDPLL}	1.5	V
I/O supply voltage	V_{DDIO}	-0.2 to 4.0	V
Input voltage	V_{IN}	(GND - 0.2) to 4.0	V
Reference voltage	V_{REF}	4.0	V
Maximum operating temperature	T_J	105	°C
Minimum operating temperature	T_A	-40	°C
Storage temperature range	T_{STG}	-55 to +150	°C
Notes: <ol style="list-style-type: none"> 1. Functional operating conditions are given in Table 3. 2. Absolute maximum ratings are stress ratings only, and functional operation at the maximum is not guaranteed. Stress beyond the listed limits may affect device reliability or cause permanent damage. 3. Section 3.1, <i>Thermal Design Considerations</i> includes a formula for computing the chip junction temperature (T_J). 			

2.2 Recommended Operating Conditions

Table 3 lists recommended operating conditions. Proper device operation outside of these conditions is not guaranteed.

Table 3. Recommended Operating Conditions

Rating	Symbol	Value	Unit
Core supply voltage	V_{DDC}	1.14 to 1.26	V
Memory supply voltage	V_{DDM}	2.38 to 2.63	V
PLL supply voltage	V_{DDPLL}	1.14 to 1.26	V
I/O supply voltage	V_{DDIO}	3.14 to 3.47	V
Reference voltage	V_{REF}	1.19 to 1.31	V
Operating temperature range	T_J	maximum: 105	°C
	T_A	minimum: -40	°C

2.3 Thermal Characteristics

Table 4 describes thermal characteristics of the MSC7116 for the MAP-BGA package.

Table 4. Thermal Characteristics for MAP-BGA Package

Characteristic	Symbol	MAP-BGA 17 × 17 mm ⁵		Unit
		Natural Convection	200 ft/min (1 m/s) airflow	
Junction-to-ambient ^{1, 2}	R _{θJA}	39	31	°C/W
Junction-to-ambient, four-layer board ^{1, 3}	R _{θJA}	23	20	°C/W
Junction-to-board ⁴	R _{θJB}	12		°C/W
Junction-to-case ⁵	R _{θJC}	7		°C/W
Junction-to-package-top ⁶	Ψ _{JT}	2		°C/W
Notes: <ol style="list-style-type: none"> Junction temperature is a function of die size, on-chip power dissipation, package thermal resistance, mounting site (board temperature, ambient temperature, air flow, power dissipation of other components on the board, and board thermal resistance). Per SEMI G38-87 and JEDEC JESD51-2 with the single layer board horizontal. Per JEDEC JESD51-6 with the board horizontal. Thermal resistance between the die and the printed circuit board per JEDEC JESD 51-8. Board temperature is measured on the top surface of the board near the package. Thermal resistance between the die and the case top surface as measured by the cold plate method (MIL SPEC-883 Method 1012.1). Thermal characterization parameter indicating the temperature difference between package top and the junction temperature per JEDEC JESD51-2. 				

Section 3.1, *Thermal Design Considerations* explains these characteristics in detail.

2.4 DC Electrical Characteristics

This section describes the DC electrical characteristics for the MSC7116.

Note: The leakage current is measured for nominal voltage values must vary in the same direction (for example, both V_{DDIO} and V_{DDC} vary by +2 percent or both vary by -2 percent).

Table 5. DC Electrical Characteristics

Characteristic	Symbol	Min	Typical	Max	Unit
Core and PLL voltage	V _{DDC} V _{DDPLL}	1.14	1.2	1.26	V
DRAM interface I/O voltage ¹	V _{DDM}	2.375	2.5	2.625	V
I/O voltage	V _{DDIO}	3.135	3.3	3.465	V
DRAM interface I/O reference voltage ²	V _{REF}	0.49 × V _{DDM}	1.25	0.51 × V _{DDM}	V
DRAM interface I/O termination voltage ³	V _{TT}	V _{REF} - 0.04	V _{REF}	V _{REF} + 0.04	V
Input high CLKIN voltage	V _{IHCLK}	2.4	3.0	3.465	V
DRAM interface input high I/O voltage	V _{IHM}	V _{REF} + 0.28	V _{DDM}	V _{DDM} + 0.3	V
DRAM interface input low I/O voltage	V _{ILM}	-0.3	GND	V _{REF} - 0.18	V
Input leakage current, V _{IN} = V _{DDIO}	I _{IN}	-1.0	0.09	1	μA
V _{REF} input leakage current	I _{VREF}	—	—	5	μA

Table 5. DC Electrical Characteristics (continued)

Characteristic	Symbol	Min	Typical	Max	Unit
Tri-state (high impedance off state) leakage current, $V_{IN} = V_{DDIO}$	I_{OZ}	-1.0	0.09	1	μA
Signal low input current, $V_{IL} = 0.4 V$	I_L	-1.0	0.09	1	μA
Signal high input current, $V_{IH} = 2.0 V$	I_H	-1.0	0.09	1	μA
Output high voltage, $I_{OH} = -2 mA$, except open drain pins	V_{OH}	2.0	3.0	—	V
Output low voltage, $I_{OL} = 5 mA$	V_{OL}	—	0	0.4	V
Typical power at 266 MHz ⁵	P	—	293.0	—	mW
Notes: <ol style="list-style-type: none"> 1. The value of V_{DDM} at the MSC7116 device must remain within 50 mV of V_{DDM} at the DRAM device at all times. 2. V_{REF} must be equal to 50% of V_{DDM} and track V_{DDM} variations as measured at the receiver. Peak-to-peak noise must not exceed $\pm 2\%$ of the DC value. 3. V_{TT} is not applied directly to the MSC7116 device. It is the level measured at the far end signal termination. It should be equal to V_{REF}. This rail should track variations in the DC level of V_{REF}. 4. Output leakage for the memory interface is measured with all outputs disabled, $0 V \leq V_{OUT} \leq V_{DDM}$. 5. The core power values were measured using a standard EFR pattern at typical conditions (25°C, 300 MHz, 1.2 V core). 					

Table 6 lists the DDR DRAM capacitance.

Table 6. DDR DRAM Capacitance

Parameter/Condition	Symbol	Max	Unit
Input/output capacitance: DQ, DQS	C_{IO}	30	pF
Delta input/output capacitance: DQ, DQS	C_{DIO}	30	pF
Note: These values were measured under the following conditions: <ul style="list-style-type: none"> • $V_{DDM} = 2.5 V \pm 0.125 V$ • $f = 1 MHz$ • $T_A = 25^\circ C$ • $V_{OUT} = V_{DDM}/2$ • V_{OUT} (peak to peak) = 0.2 V 			

2.5.2 Configuring Clock Frequencies

This section describes important requirements for configuring clock frequencies in the MSC7116 device when using the PLL block. To configure the device clocking, you must program four fields in the Clock Control Register (CLKCTL):

- *PLLDVF field.* Specifies the PLL division factor ($PLLDVF + 1$) to divide the input clock frequency F_{CLKIN} . The output of the divider block is the input to the multiplier block.
- *PLLMLTF field.* Specifies the PLL multiplication factor ($PLLMLTF + 1$). The output from the multiplier block is the loop frequency F_{LOOP} .
- *RNG field.* Selects the available PLL frequency range for F_{VCO} , either F_{LOOP} when the RNG bit is set (1) or $F_{LOOP}/2$ when the RNG bit is cleared (0).
- *CKSEL field.* Selects F_{CLKIN} , F_{VCO} , or $F_{VCO}/2$ as the source for the core clock.

There are restrictions on the frequency range permitted at the beginning of the multiplication portion of the PLL that affect the allowable values for the PLLDVF and PLLMLTF fields. The following sections define these restrictions and provide guidelines to configure the device clocking when using the PLL. Refer to the Clock and Power Management chapter in the *MSC711x Reference Manual* for details on the clock programming model.

2.5.2.1 PLL Multiplier Restrictions

There are two restrictions for correct usage of the PLL block:

- The input frequency to the PLL multiplier block (that is, the output of the divider) must be in the range 10–25 MHz.
- The output frequency of the PLL multiplier must be in the range 266–532 MHz.

When programming the PLL for a desired output frequency using the PLLDVF, PLLMLTF, and RNG fields, you must meet these constraints.

2.5.2.2 Input Division Factors and Corresponding CLKIN Frequency Range

The value of the PLLDVF field determines the allowable CLKIN frequency range, as shown in **Table 9**.

Table 9. CLKIN Frequency Ranges by Divide Factor Value

PLLDVF Field Value	Input Divide Factor	CLKIN Frequency Range	Comments
0x00	1	10 to 25 MHz	Input Division by 1
0x01	2	20 to 50 MHz	Input Division by 2
0x02	3	30 to 75 MHz	Input Division by 3
0x03	4	40 to 100 MHz	Input Division by 4
0x04	5	50 to 100 MHz	Input Division by 5
0x05	6	60 to 100 MHz	Input Division by 6
0x06	7	70 to 100 MHz	Input Division by 7
0x07	8	80 to 100 MHz	Input Division by 8
0x08	9	90 to 100 MHz	Input Division by 9
0x09	10	100 MHz	Input Division by 10

Note: The maximum CLKIN frequency is 100 MHz. Therefore, the PLLDVF value must be in the range from 1–10.

2.5.4 DDR DRAM Controller Timing

This section provides the AC electrical characteristics for the DDR DRAM interface.

2.5.4.1 DDR DRAM Input AC Timing Specifications

Table 17 provides the input AC timing specifications for the DDR DRAM interface.

Table 17. DDR DRAM Input AC Timing

No.	Parameter	Symbol	Min	Max	Unit
—	AC input low voltage	V_{IL}	—	$V_{REF} - 0.31$	V
—	AC input high voltage	V_{IH}	$V_{REF} + 0.31$	$V_{DDM} + 0.3$	V
201	Maximum Dn input setup skew relative to DQSn input	—	—	900	ps
202	Maximum Dn input hold skew relative to DQSn input	—	—	900	ps
Notes: <ol style="list-style-type: none"> Maximum possible skew between a data strobe (DQSn) and any corresponding bit of data (D[8n + {0...7}] if $0 \leq n \leq 7$). See Table 18 for t_{CK} value. Dn should be driven at the same time as DQSn. This is necessary because the DQSn centering on the DQn data tenure is done internally. 					

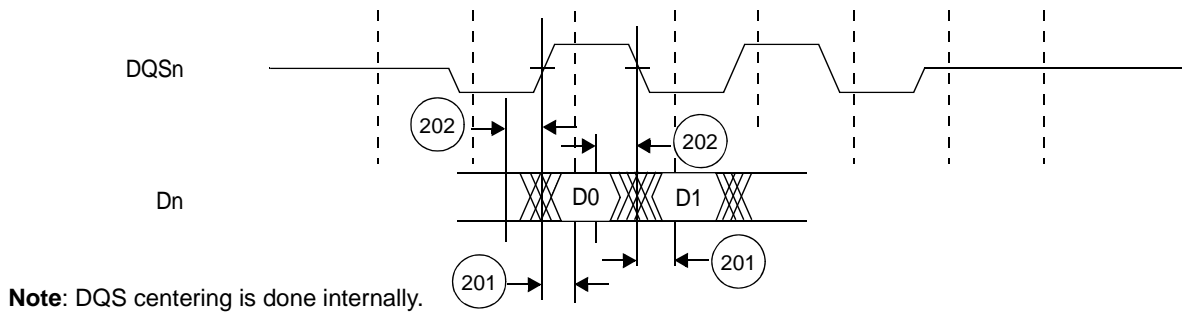


Figure 5. DDR DRAM Input Timing Diagram

2.5.4.2 DDR DRAM Output AC Timing Specifications

Table 18 and Table 19 list the output AC timing specifications and measurement conditions for the DDR DRAM interface.

Table 18. DDR DRAM Output AC Timing

No.	Parameter	Symbol	Min	Max	Unit
200	CK cycle time, (CK/ \overline{CK} crossing) ¹ • 100 MHz (DDR200) • 150 MHz (DDR300)	t_{CK}	10 6.67	— —	ns ns
204	$\overline{An}/\overline{RAS}/\overline{CAS}/\overline{WE}/\overline{CKE}$ output setup with respect to CK	t_{DDKHAS}	$0.5 \times t_{CK} - 1000$	—	ps
205	$\overline{An}/\overline{RAS}/\overline{CAS}/\overline{WE}/\overline{CKE}$ output hold with respect to CK	t_{DDKHAX}	$0.5 \times t_{CK} - 1000$	—	ps
206	\overline{CSn} output setup with respect to CK	t_{DDKHCS}	$0.5 \times t_{CK} - 1000$	—	ps
207	\overline{CSn} output hold with respect to CK	$t_{DDKHCSX}$	$0.5 \times t_{CK} - 1000$	—	ps
208	CK to DQSn ²	t_{DDKMHM}	-600	600	ps

Table 18. DDR DRAM Output AC Timing (continued)

No.	Parameter	Symbol	Min	Max	Unit
209	Dn/DQMn output setup with respect to DQSn ³	t_{DDKHDS} , t_{DDKLDS}	$0.25 \times t_{CK} - 750$	—	ps
210	Dn/DQMn output hold with respect to DQSn ³	t_{DDKHDX} , t_{DDKLDX}	$0.25 \times t_{CK} - 750$	—	ps
211	DQSn preamble start ⁴	t_{DDKHMP}	$-0.25 \times t_{CK}$	—	ps
212	DQSn epilogue end ⁵	t_{DDKHME}	-600	600	ps

- Notes:**
- All CK/ \overline{CK} referenced measurements are made from the crossing of the two signals ± 0.1 V.
 - t_{DDKHMH} can be modified through the TCFG2[WRDD] DQSS override bits. The DRAM requires that the first write data strobe arrives 75–125% of a DRAM cycle after the write command is issued. Any skew between DQSn and CK must be considered when trying to achieve this 75%–125% goal. The TCFG2[WRDD] bits can be used to shift DQSn by 1/4 DRAM cycle increments. The skew in this case refers to an internal skew existing at the signal connections. By default, the CK/ \overline{CK} crossing occurs in the middle of the control signal ($A_n/\overline{RAS}/\overline{CAS}/\overline{WE}/\overline{CKE}$) tenure. Setting TCFG2[ACSM] bit shifts the control signal assertion 1/2 DRAM cycle earlier than the default timing. This means that the signal is asserted no earlier than 600 ps before the CK/ \overline{CK} crossing and no later than 600 ps after the crossing time; the device uses 1200 ps of the skew budget (the interval from -600 to +600 ps). Timing is verified by referencing the falling edge of CK. See Chapter 10 of the *MSC711x Reference Manual* for details.
 - Determined by maximum possible skew between a data strobe (DQS) and any corresponding bit of data. The data strobe should be centered inside of the data eye.
 - Please note that this spec is in reference to the DQSn first rising edge. It could also be referenced from CK(r), but due to programmable delay of the write strobes (TCFG2[WRDD]), there pre-amble may be extended for a full DRAM cycle. For this reason, we reference from DQSn.
 - All outputs are referenced to the rising edge of CK. Note that this is essentially the CK/DQSn skew in spec 208. In addition there is no real “maximum” time for the epilogue end. JEDEC does not require this is as a device limitation, but simply for the chip to guarantee fast enough write-to-read turn-around times. This is already guaranteed by the memory controller operation.

Figure 6 shows the DDR DRAM output timing diagram.

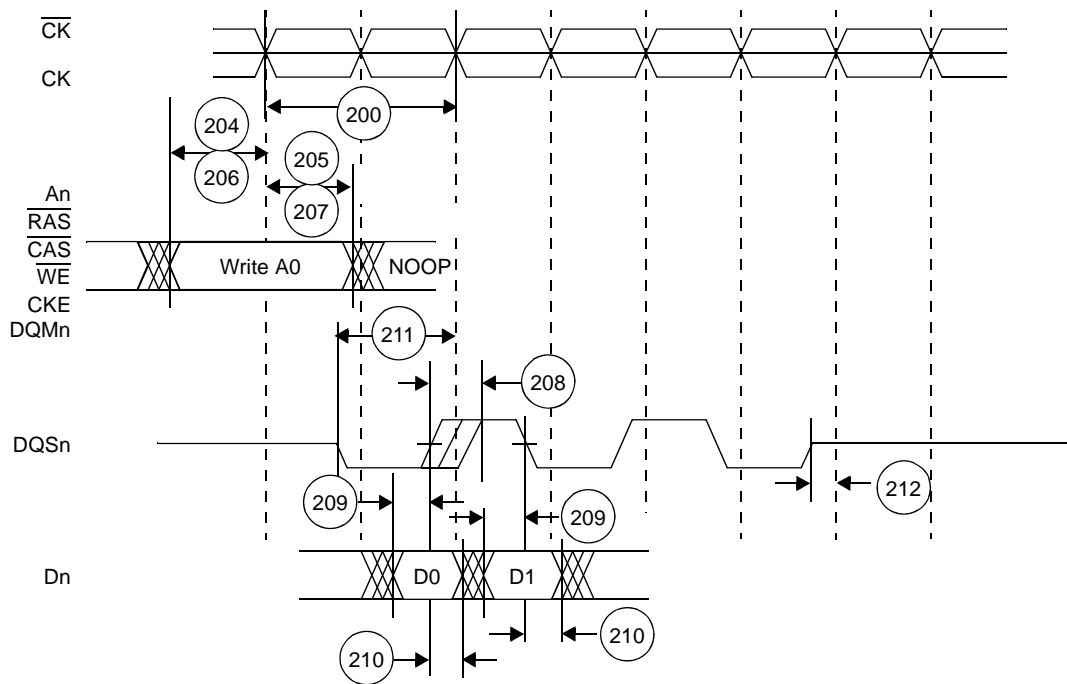


Figure 6. DDR DRAM Output Timing Diagram

2.5.7 HDI16 Signals

Table 25. Host Interface (HDI16) Timing^{1, 2}

No.	Characteristics ³	Expression	Value	Unit
40	Host Interface Clock period	T_{CORE}	Note 1	ns
44a	Read data strobe minimum assertion width ⁴ HACK read minimum assertion width	$2.0 \times T_{CORE} + 9.0$	Note 11	ns
44b	Read data strobe minimum deassertion width ⁴ HACK read minimum deassertion width	$1.5 \times T_{CORE}$	Note 11	ns
44c	Read data strobe minimum deassertion width ⁴ after "Last Data Register" reads ^{5,6} , or between two consecutive CVR, ICR, or ISR reads ⁷ HACK minimum deassertion width after "Last Data Register" reads ^{5,6}	$2.5 \times T_{CORE}$	Note 11	ns
45	Write data strobe minimum assertion width ⁸ HACK write minimum assertion width	$1.5 \times T_{CORE}$	Note 11	ns
46	Write data strobe minimum deassertion width ⁸ HACK write minimum deassertion width after ICR, CVR and Data Register writes ⁵	$2.5 \times T_{CORE}$	Note 11	ns
47	Host data input minimum setup time before write data strobe deassertion ⁸ Host data input minimum setup time before HACK write deassertion	—	2.5	ns
48	Host data input minimum hold time after write data strobe deassertion ⁸ Host data input minimum hold time after HACK write deassertion	—	2.5	ns
49	Read data strobe minimum assertion to output data active from high impedance ⁴ HACK read minimum assertion to output data active from high impedance	—	1.0	ns
50	Read data strobe maximum assertion to output data valid ⁴ HACK read maximum assertion to output data valid	$(2.0 \times T_{CORE}) + 8.0$	Note 11	ns
51	Read data strobe maximum deassertion to output data high impedance ⁴ HACK read maximum deassertion to output data high impedance	—	9.0	ns
52	Output data minimum hold time after read data strobe deassertion ⁴ Output data minimum hold time after HACK read deassertion	—	1.0	ns
53	HCS[1–2] minimum assertion to read data strobe assertion ⁴	—	0.5	ns
54	HCS[1–2] minimum assertion to write data strobe assertion ⁸	—	0.0	ns
55	HCS[1–2] maximum assertion to output data valid	$(2.0 \times T_{CORE}) + 6.0$	Note 11	ns
56	HCS[1–2] minimum hold time after data strobe deassertion ⁹	—	0.5	ns
57	HA[0–2], HRW minimum setup time before data strobe assertion ⁹	—	5.0	ns
58	HA[0–2], HRW minimum hold time after data strobe deassertion ⁹	—	5.0	ns
61	Maximum delay from read data strobe deassertion to host request deassertion for "Last Data Register" read ^{4, 5, 10}	$(3.0 \times T_{CORE}) + 6.0$	Note 11	ns
62	Maximum delay from write data strobe deassertion to host request deassertion for "Last Data Register" write ^{5,8,10}	$(3.0 \times T_{CORE}) + 6.0$	Note 11	ns
63	Minimum delay from DMA HACK (OAD=0) or Read/Write data strobe(OAD=1) deassertion to HREQ assertion.	$(2.0 \times T_{CORE}) + 1.0$	Note 11	ns
64	Maximum delay from DMA HACK (OAD=0) or Read/Write data strobe(OAD=1) assertion to HREQ deassertion	$(5.0 \times T_{CORE}) + 6.0$	Note 11	ns
Notes:	<ol style="list-style-type: none"> T_{CORE} = core clock period. At 300 MHz, T_{CORE} = 3.333 ns. In the timing diagrams below, the controls pins are drawn as active low. The pin polarity is programmable. $V_{DD} = 3.3 \text{ V} \pm 0.15 \text{ V}$; $T_J = -40^\circ\text{C}$ to $+105^\circ\text{C}$, $C_L = 30 \text{ pF}$ for maximum delay timings and $C_L = 0 \text{ pF}$ for minimum delay timings. The read data strobe is HRD/HRD in the dual data strobe mode and HDS/HDS in the single data strobe mode. For 64-bit transfers, the "last data register" is the register at address 0x7, which is the last location to be read or written in data transfers. This is RX0/TX0 in the little endian mode (HBE = 0), or RX3/TX3 in the big endian mode (HBE = 1). This timing is applicable only if a read from the "last data register" is followed by a read from the RX[0–3] registers without first polling RXDF or HREQ bits, or waiting for the assertion of the HREQ/HREQ signal. This timing is applicable only if two consecutive reads from one of these registers are executed. The write data strobe is HWR in the dual data strobe mode and HDS in the single data strobe mode. The data strobe is host read (HRD/HRD) or host write (HWR/HWR) in the dual data strobe mode and host data strobe (HDS/HDS) in the single data strobe mode. The host request is HREQ/HREQ in the single host request mode and HRRQ/HRRQ and HTRQ/HTRQ in the double host request mode. HRRQ/HRRQ is deasserted only when HOTX fifo is empty, HTRQ/HTRQ is deasserted only if HORX fifo is full Compute the value using the expression. The read and write data strobe minimum deassertion width for non-"last data register" accesses in single and dual data strobe modes is based on timings 57 and 58. 			

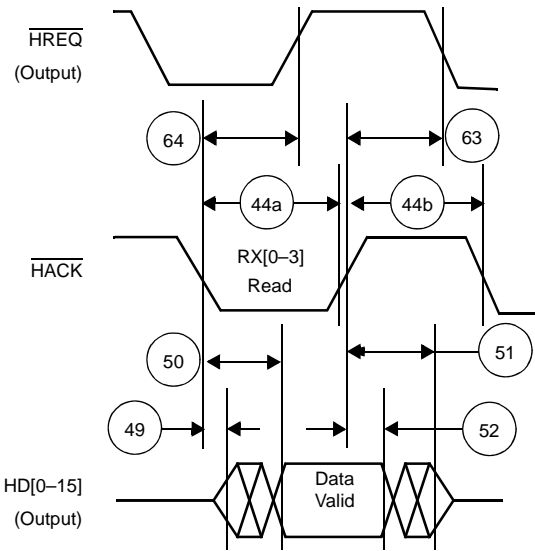


Figure 18. Host DMA Read Timing Diagram, HPCR[OAD] = 0

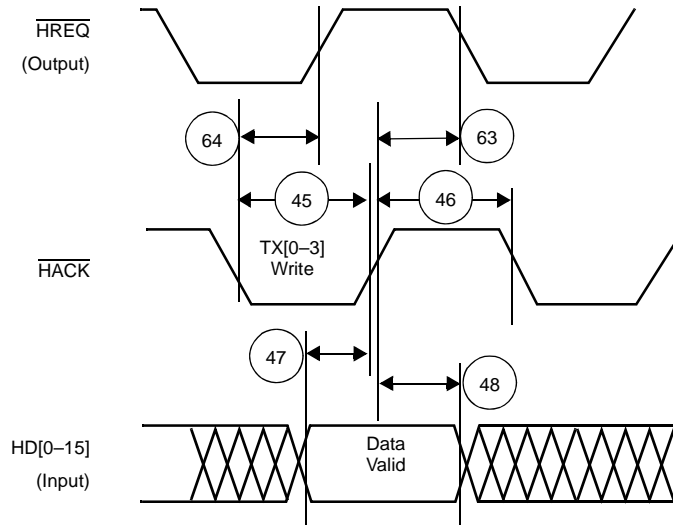


Figure 19. Host DMA Write Timing Diagram, HPCR[OAD] = 0

2.5.11 Event Timing

Table 29. EVNT Signal Timing

Number	Characteristics	Type	Min
67	EVNT as input	Asynchronous	1.5 × APBCLK periods
68	EVNT as output	Synchronous to core clock	1 APBCLK period

Notes:

1. Refer to **Table 27** for a definition of the APBCLK period.
2. Direction of the EVNT signal is configured through the GPIO and Event port registers.
3. Refer to the signal chapter in the *MSC711x Reference Manual* for details on EVNT pin functionality.

Figure 24 shows the signal behavior of the EVNT pins.

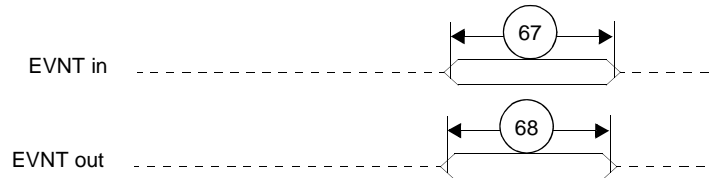


Figure 24. EVNT Pin Timing

2.5.12 GPIO Timing

Table 30. GPIO Signal Timing^{1,2,3}

Number	Characteristics	Type	Min
601	GPI ^{4,5}	Asynchronous	1.5 × APBCLK periods
602	GPO ⁵	Synchronous to core clock	1 APBCLK period
603	Port A edge-sensitive interrupt	Asynchronous	1.5 × APBCLK periods
604	Port A level-sensitive interrupt	Asynchronous	3 × APBCLK periods ⁶

Notes:

1. Refer to **Table 27** for a definition of the APBCLK period.
2. Direction of the GPIO signal is configured through the GPIO port registers.
3. Refer to **Section 1.5** for details on GPIO pin functionality.
4. GPI data is synchronized to the APBCLK internally and the minimum listed is the capability of the hardware to capture data into a register when the GPADR is read. The specification is not tested due to the asynchronous nature of the input and dependence on the state of the DSP core. It is guaranteed by design.
5. The output signals cannot toggle faster than 75 MHz.
6. Level-sensitive interrupts should be held low until the system determines (via the service routine) that the interrupt is acknowledged.

Figure 25 shows the signal behavior of the GPI/GPO pins.

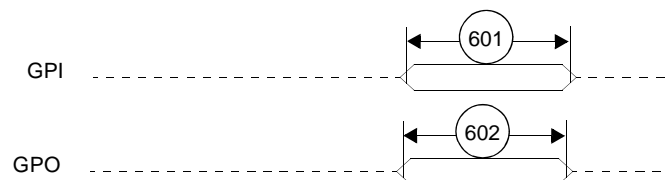


Figure 25. GPI/GPO Pin Timing

2.5.13 JTAG Signals

Table 31. JTAG Timing

No.	Characteristics	All frequencies		Unit
		Min	Max	
700	TCK frequency of operation ($1/(T_C \times 3)$) Note: $T_C = 1/\text{CLOCK}$ which is the period of the core clock. The TCK frequency must less than 1/3 of the core frequency with an absolute maximum limit of 40 MHz.	0.0	40.0	MHz
701	TCK cycle time	25.0	—	ns
702	TCK clock pulse width measured at $V_M = 1.6\text{ V}$	11.0	—	ns
703	TCK rise and fall times	0.0	3.0	ns
704	Boundary scan input data set-up time	5.0	—	ns
705	Boundary scan input data hold time	14.0	—	ns
706	TCK low to output data valid	0.0	20.0	ns
707	TCK low to output high impedance	0.0	20.0	ns
708	TMS, TDI data set-up time	5.0	—	ns
709	TMS, TDI data hold time	14.0	—	ns
710	TCK low to TDO data valid	0.0	24.0	ns
711	TCK low to TDO high impedance	0.0	10.0	ns
712	$\overline{\text{TRST}}$ assert time	100.0	—	ns

Note: All timings apply to OCE module data transfers as the OCE module uses the JTAG port as an interface.

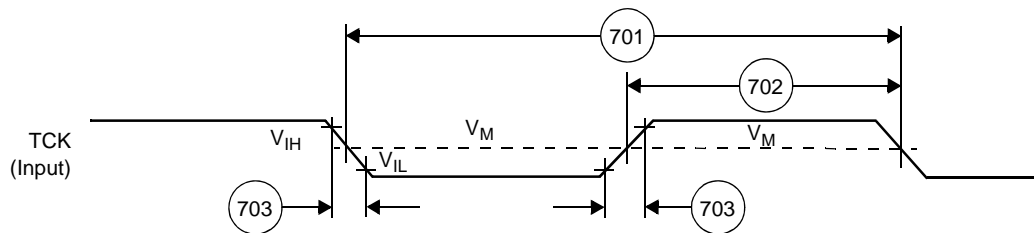


Figure 26. Test Clock Input Timing Diagram

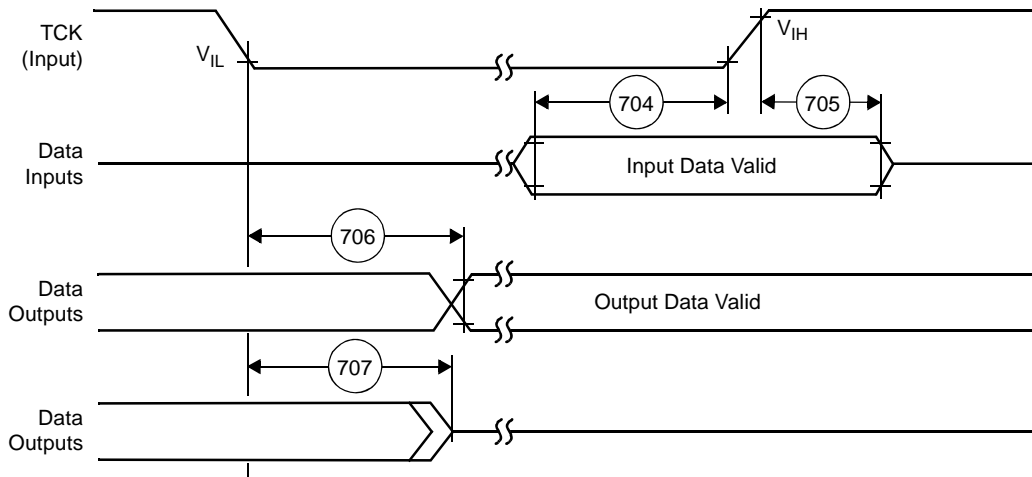


Figure 27. Boundary Scan (JTAG) Timing Diagram

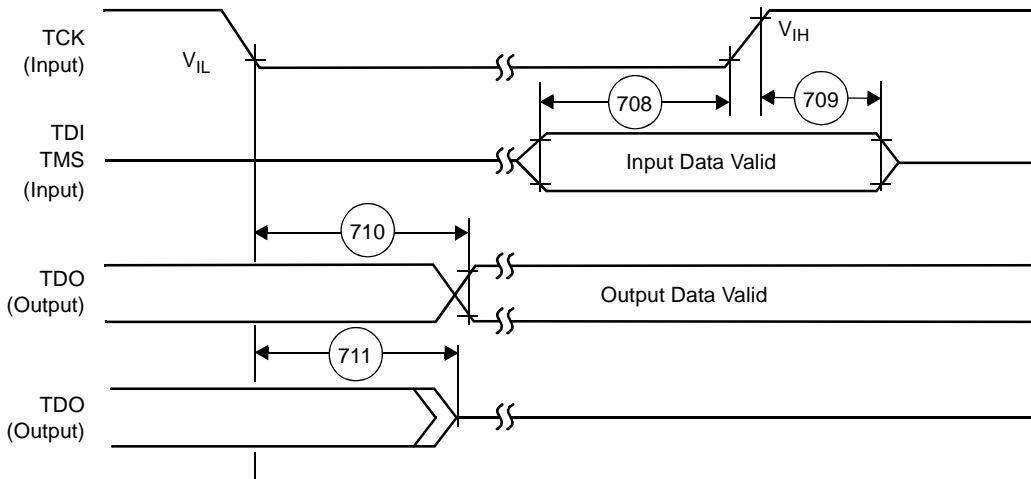


Figure 28. Test Access Port Timing Diagram



Figure 29. TRST Timing Diagram

3.2.2.1 Case 1

The power-up sequence is as follows:

1. Turn on the V_{DDIO} (3.3 V) supply first.
2. Turn on the V_{DDC} (1.2 V) supply second.
3. Turn on the V_{DDM} (2.5 V) supply third.
4. Turn on the V_{REF} (1.25 V) supply fourth (last).

The power-down sequence is as follows:

1. Turn off the V_{REF} (1.25 V) supply first.
2. Turn off the V_{DDM} (2.5 V) supply second.
3. Turn off the V_{DDC} (1.2 V) supply third.
4. Turn off the V_{DDIO} (3.3 V) supply fourth (last).

Use the following guidelines:

- Make sure that the time interval between the ramp-down of V_{DDIO} and V_{DDC} is less than 10 ms.
- Make sure that the time interval between the ramp-up or ramp-down for V_{DDC} and V_{DDM} is less than 10 ms for power-up and power-down.
- Refer to **Figure 30** for relative timing for power sequencing case 1.

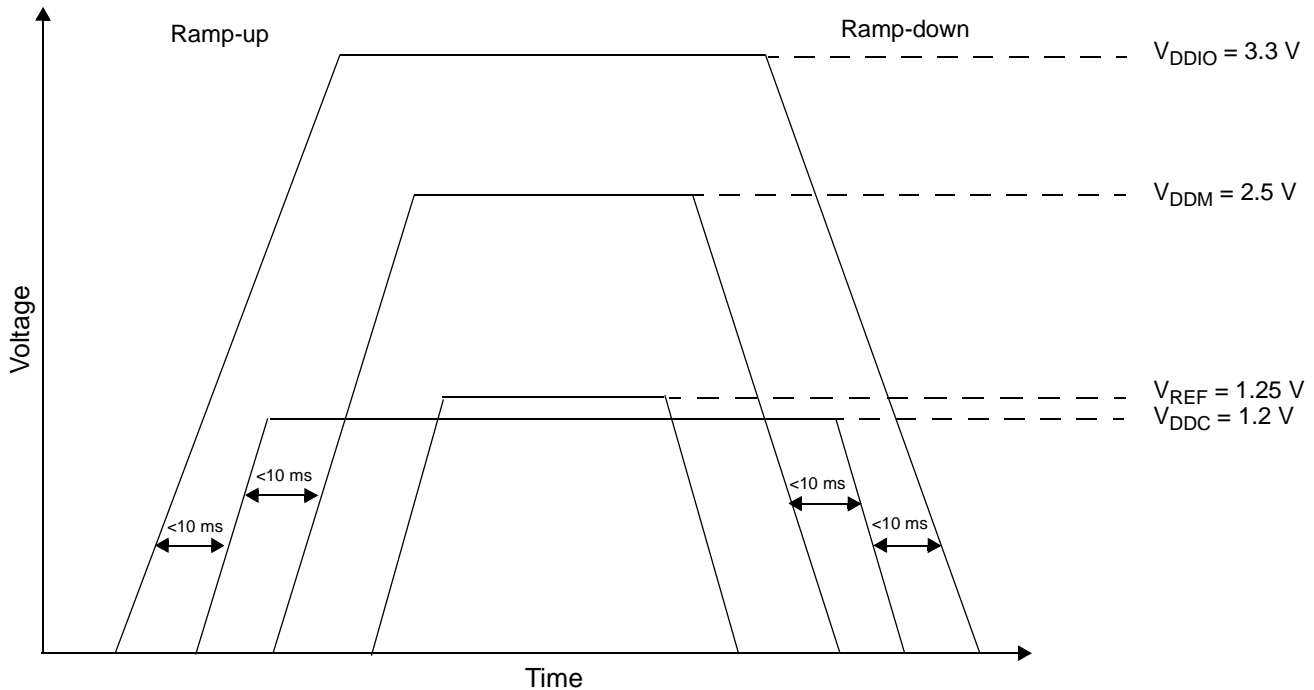


Figure 30. Voltage Sequencing Case 1

3.2.2.2 Case 2

The power-up sequence is as follows:

1. Turn on the V_{DDIO} (3.3 V) supply first.
2. Turn on the V_{DDC} (1.2 V) and V_{DDM} (2.5 V) supplies simultaneously (second).
3. Turn on the V_{REF} (1.25 V) supply last (third).

Note: Make sure that the time interval between the ramp-up of V_{DDIO} and V_{DDC}/V_{DDM} is less than 10 ms.

The power-down sequence is as follows:

1. Turn off the V_{REF} (1.25 V) supply first.
2. Turn off the V_{DDM} (2.5 V) supply second.
3. Turn off the V_{DDC} (1.2 V) supply third.
4. Turn off the V_{DDIO} (3.3 V) supply fourth (last).

Use the following guidelines:

- Make sure that the time interval between the ramp-down for V_{DDIO} and V_{DDC} is less than 10 ms.
- Make sure that the time interval between the ramp-up or ramp-down for V_{DDC} and V_{DDM} is less than 10 ms for power-up and power-down.
- Refer to **Figure 31** for relative timing for Case 2.

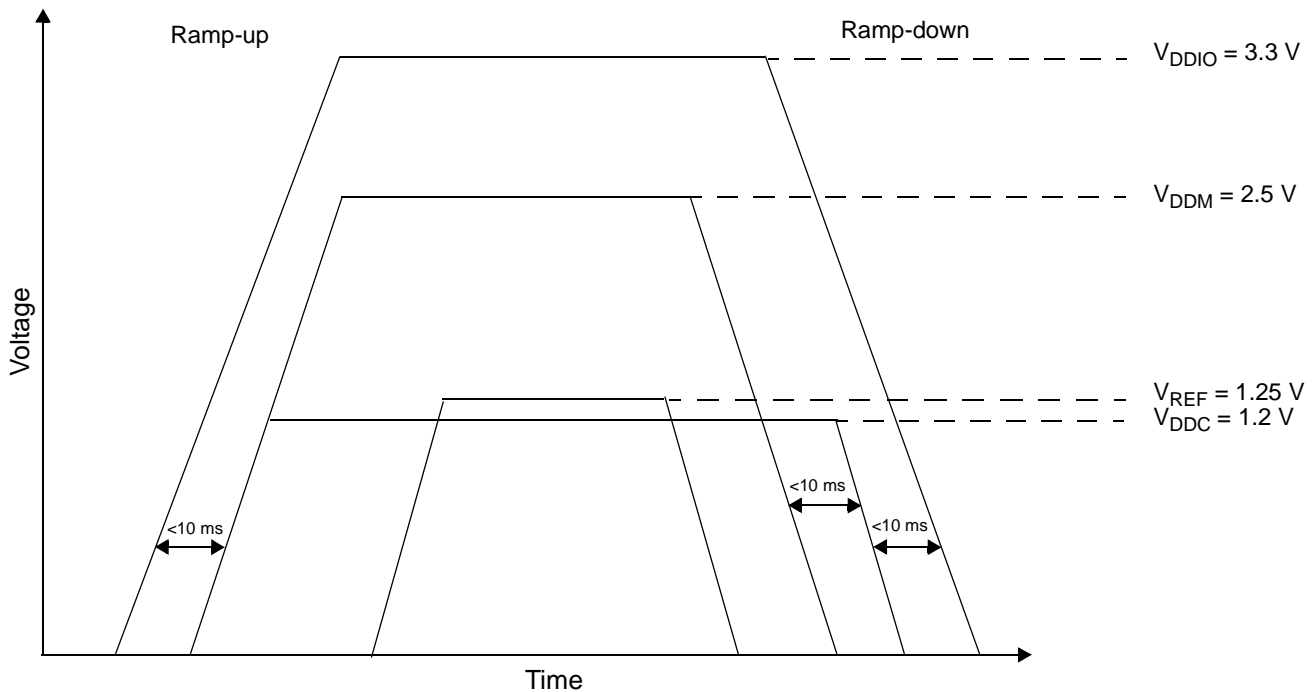


Figure 31. Voltage Sequencing Case 2

3.2.2.5 Case 5 (not recommended for new designs)

The power-up sequence is as follows:

1. Turn on the V_{DDIO} (3.3 V) supply first.
2. Turn on the V_{DDM} (2.5 V) supply second.
3. Turn on the V_{DDC} (1.2 V) supply third.
4. Turn on the V_{REF} (1.25 V) supply fourth (last).

Note: Make sure that the time interval between the ramp-up of V_{DDIO} and V_{DDM} is less than 10 ms.

The power-down sequence is as follows:

1. Turn off the V_{REF} (1.25 V) supply first.
2. Turn off the V_{DDC} (1.2 V) supply second.
3. Turn off the V_{DDM} (2.5 V) supply third.
4. Turn off the V_{DDIO} (3.3 V) supply fourth (last).

Use the following guidelines:

- Make sure that the time interval between the ramp-down of V_{DDIO} and V_{DDM} is less than 10 ms.
- Make sure that the time interval between the ramp-up or ramp-down for V_{DDC} and V_{DDM} is less than 2 ms for power-up and power-down.
- Refer to **Figure 34** for relative timing for power sequencing case 5.

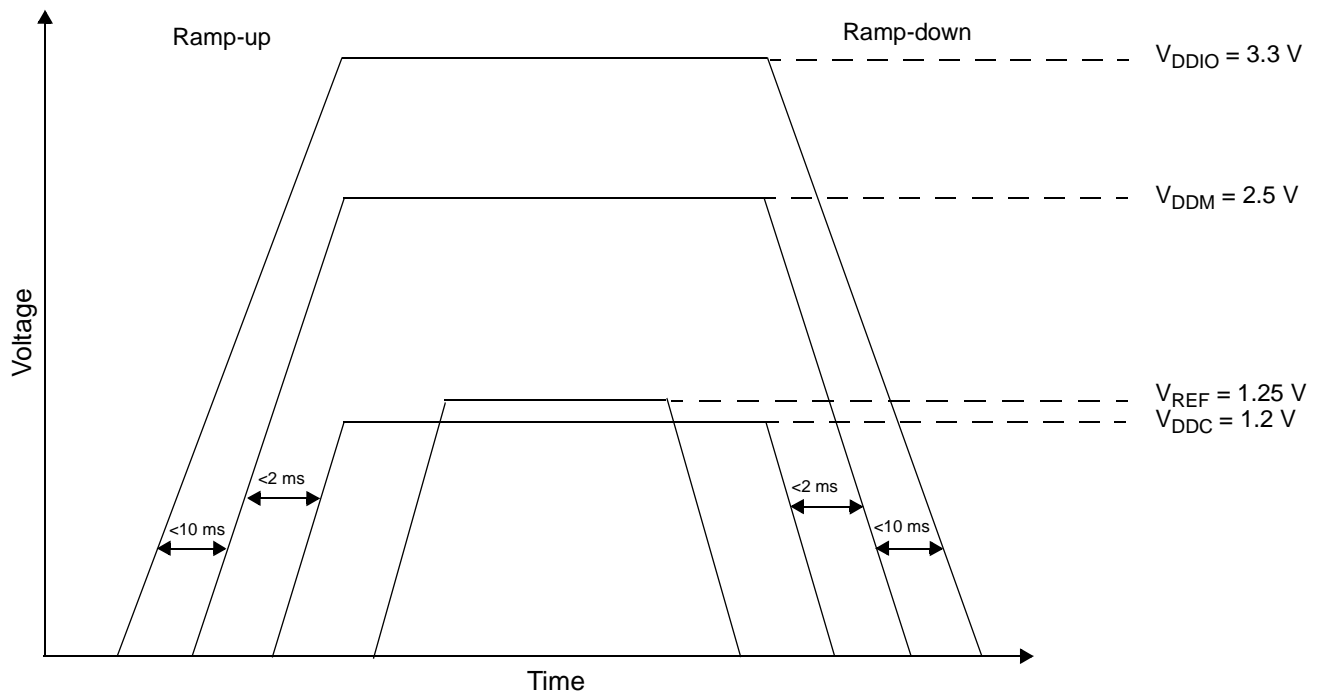


Figure 34. Voltage Sequencing Case 5

Note: Cases 1, 2, 3, and 4 are recommended for system design. Designs that use Case 5 may have large current spikes on the V_{DDM} supply at startup and is not recommended for most designs. If a design uses case 5, it must accommodate the potential current spikes. Verify risks related to current spikes using actual information for the specific application.

3.2.3 Power Planes

Each power supply pin (V_{DDC} , V_{DDM} , and V_{DDIO}) should have a low-impedance path to the board power supply. Each GND pin should be provided with a low-impedance path to ground. The power supply pins drive distinct groups of logic on the device. The MSC7116 V_{DDC} power supply pins should be bypassed to ground using decoupling capacitors. The capacitor leads and associated printed circuit traces connecting to device power pins and GND should be kept to less than half an inch per capacitor lead. A minimum four-layer board that employs two inner layers as power and GND planes is recommended. See **Section 3.5** for DDR Controller power guidelines.

3.2.4 Decoupling

Both the I/O voltage and core voltage should be decoupled for switching noise. For I/O decoupling, use standard capacitor values of $0.01 \mu\text{F}$ for every two to three voltage pins. For core voltage decoupling, use two levels of decoupling. The first level should consist of a $0.01 \mu\text{F}$ high frequency capacitor with low effective series resistance (ESR) and effective series inductance (ESL) for every two to three voltage pins. The second decoupling level should consist of two bulk/tantalum decoupling capacitors, one $10 \mu\text{F}$ and one $47 \mu\text{F}$, (with low ESR and ESL) mounted as closely as possible to the MSC7116 voltage pins. Additionally, the maximum drop between the power supply and the DSP device should be 15 mV at 1 A .

3.2.5 PLL Power Supply Filtering

The MSC7116 V_{DDPLL} power signal provides power to the clock generation PLL. To ensure stability of the internal clock, the power supplied to this pin should be filtered with capacitors that have low and high frequency filtering characteristics. V_{DDPLL} can be connected to V_{DDC} through a 2Ω resistor. V_{SSPLL} can be tied directly to the GND plane. A circuit similar to the one shown in **Figure 35** is recommended. The PLL loop filter should be placed as closely as possible to the V_{DDPLL} pin (which are located on the outside edge of the silicon package) to minimize noise coupled from nearby circuits. The $0.01 \mu\text{F}$ capacitor should be closest to V_{DDPLL} , followed by the $0.1 \mu\text{F}$ capacitor, the $10 \mu\text{F}$ capacitor, and finally the $2\text{-}\Omega$ resistor to V_{DDC} . These traces should be kept short.

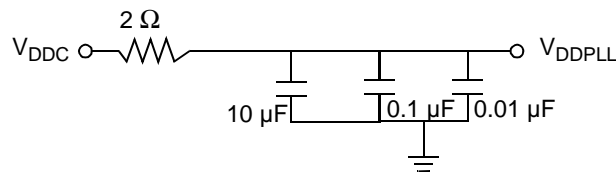


Figure 35. PLL Power Supply Filter Circuits

3.2.6 Power Consumption

You can reduce power consumption in your design by controlling the power consumption of the following regions of the device:

- *Extended core.* Use the SC1400 Stop and Wait modes by issuing a **stop** or **wait** instruction.
- *Clock synthesis module.* Disable the PLL, timer, watchdog, or DDR clocks or disable the CLK0 pin.
- *AHB subsystem.* Freeze or shut down the AHB subsystem using the GPSCTL[XBR_HRQ] bit.
- *Peripheral subsystem.* Halt the individual on-device peripherals such as the DDR memory controller, Ethernet MAC, HDI16, TDM, UART, I²C, and timer modules.

For details, see the “Clocks and Power Management” chapter of the *MSC711x Reference Manual*.

3.3.2 Peripheral Power

Peripherals include the DDR memory controller, Ethernet controller, DMA controller, HDI16, TDM, UART, timers, GPIOs, and the I²C module. Basic power consumption by each module is assumed to be the same and is computed by using the following equation which assumes an effective load of 20 pF, core voltage swing of 1.2 V, and a switching frequency of 133 MHz. This yields:

$$P_{PERIPHERAL} = 20 \text{ pF} \times (1.2 \text{ V})^2 \times 133 \text{ MHz} \times 10^{-3} = 3.83 \text{ mW per peripheral} \quad \text{Eqn. 6}$$

Multiply this value by the number of peripherals used in the application to compute the total peripheral power consumption.

3.3.3 External Memory Power

Estimation of power consumption by the DDR memory system is complex. It varies based on overall system signal line usage, termination and load levels, and switching rates. Because the DDR memory includes terminations external to the MSC7116 device, the 2.5 V power source provides the power for the termination, which is a static value of 16 mA per signal driven high. The dynamic power is computed, however, using a differential voltage swing of ± 0.200 V, yielding a peak-to-peak swing of 0.4 V. The equations for computing the DDR power are:

$$P_{DDRIO} = P_{STATIC} + P_{DYNAMIC} \quad \text{Eqn. 7}$$

$$P_{STATIC} = (\text{unused pins} \times \% \text{ driven high}) \times 16 \text{ mA} \times 2.5 \text{ V} \quad \text{Eqn. 8}$$

$$P_{DYNAMIC} = (\text{pin activity value}) \times 20 \text{ pF} \times (0.4 \text{ V})^2 \times 266 \text{ MHz} \times 10^{-3} \text{ mW} \quad \text{Eqn. 9}$$

$$\text{pin activity value} = (\text{active data lines} \times \% \text{ activity} \times \% \text{ data switching}) + (\text{active address lines} \times \% \text{ activity}) \quad \text{Eqn. 10}$$

As an example, assume the following:

- unused pins = 16 (DDR uses 16-pin mode)
- % driven high = 50%
- active data lines = 16
- % activity = 60%
- % data switching = 50%
- active address lines = 3

In this example, the DDR memory power consumption is:

$$P_{DDRIO} = ((16 \times 0.5) \times 16 \times 2.5) + (((16 \times 0.6 \times 0.5) + (3 \times 0.6)) \times 20 \times (0.4)^2 \times 266 \times 10^{-3}) = 326.3 \text{ mW} \quad \text{Eqn. 11}$$

3.3.4 External I/O Power

The estimation of the I/O power is similar to the computation of the peripheral power estimates. The power consumption per signal line is computed assuming a maximum load of 20 pF, a voltage swing of 3.3 V, and a switching frequency of 33 MHz, which yields:

$$P_{IO} = 20 \text{ pF} \times (3.3 \text{ V})^2 \times 33 \text{ MHz} \times 10^{-3} = 7.19 \text{ mW per I/O line} \quad \text{Eqn. 12}$$

Multiply this number by the number of I/O signal lines used in the application design to compute the total I/O power.

Note: The signal loading depends on the board routing. For systems using a single DDR device, the load could be as low as 7 pF.

3.3.5 Leakage Power

The leakage power is for all power supplies combined at a specific temperature. The value is temperature dependent. The observed leakage value at room temperature is 64 mW.

3.3.6 Example Total Power Consumption

Using the examples in this section and assuming four peripherals and 10 I/O lines active, a total power consumption value is estimated as the following:

$$P_{TOTAL} = 287 + (4 \times 3.83) + 326.3 + (10 \times 7.19) + 64 = 764.52 \text{ mW} \quad \text{Eqn. 13}$$

3.4 Reset and Boot

This section describes the recommendations for configuring the MSC7116 at reset and boot.

3.4.1 Reset Circuit

$\overline{\text{HRESET}}$ is a bidirectional signal and, if driven as an input, should be driven with an open collector or open-drain device. For an open-drain output such as HRESET , take care when driving many buffers that implement input bus-hold circuitry. The bus-hold currents can cause enough voltage drop across the pull-up resistor to change the logic level to low. Either a smaller value of pull-up or less current loading from the bus-hold drivers overcomes this issue. To avoid exceeding the MSC7116 output current, the pull-up value should not be too small (a 1 K Ω pull-up resistor is used in the MSC711xADS reference design).

3.4.2 Reset Configuration Pins

Table 34 shows the MSC7116 reset configuration signals. These signals are sampled at the deassertion (rising edge) of $\overline{\text{PORESET}}$. For details, refer to the Reset chapter of the *MSC711x Reference Manual*.

Table 34. Reset Configuration Signals

Signal	Description	Settings
BM[3–0]	Determines boot mode.	See Table 35 for details.
SWTE	Determines watchdog functionality.	0 Watchdog timer disabled. 1 Watchdog timer enabled.
HDSP	Configures HDI16 strobe polarity.	0 Host Data strobes active low. 1 Host Data strobes active high.
H8BIT	Configures HDI16 operation mode.	0 HDI16 port configured for 16-bit operation. 1 HDI16 port configured for 8-bit operation.

Table 35. Boot Mode Source Selection

BM[3-0]	Boot Port	Input Clock Frequency	Clock Divide	PLL	CKSEL	RNG Bit	Core Clock Frequency	Comments
HDI Boot Modes								
0000	HDI16	< F _{max}	N/A	N/A	00	0	< F _{max}	Not clocked by the PLL. Can boot as 8- or 16-bit HDI.
0101	HDI16	22.2-25 MHz	1	12	11	1	266–300 MHz	Can boot as 8- or 16-bit HDI.
0010	HDI16	25-33.3 MHz	2	32	01	1	200–266 MHz	
0111	HDI16	33-66 MHz	3	12	11	1	132–264 MHz	
0100	HDI16	44.3-50 MHz	2	12	11	1	266–300 MHz	
SPI Boot Modes - Using HA3, HCS2, BM3, BM2 Pins								
1000	SPI (SW)	< F _{max}	N/A	N/A	00	0	< F _{max}	The boot program automatically determines whether EEPROM or Flash memory.
1001	SPI (SW)	15.6-25 MHz	1	17	11	0	133–212.5 MHz	
1010	SPI (SW)	33-50 MHz	2	16	11	0	132–200 MHz	
1011	SPI (SW)	44.3-75 MHz	3	18	11	0	133–225 MHz	
SPI Boot Modes - Using URXD, UTXD, SCL, SDA Pins								
1100	SPI (SW)	< F _{max}	N/A	N/A	00	0	< F _{max}	Boots through different set of pins.
I ² C Boot Modes								
0001	I ² C	< 100 MHz	N/A	N/A	00	0	< 100 MHz	Not clocked by the PLL. I ² C is limited to a maximum bit rate of 400 Kbps. With a clock divider of 128, this limits the maximum input clock frequency to 100 MHz.
Reserved								
0011	Reserved	—	—	—	—	—	—	—
0110	Reserved	—	—	—	—	—	—	—
1101	Reserved	—	—	—	—	—	—	—
1110	Reserved	—	—	—	—	—	—	—
1111	Reserved	—	—	—	—	—	—	—
Notes:	<ol style="list-style-type: none"> 1. The clock divider determines the value used in the clock module CLKCTRL[PLLDVDF] field. 2. The clock multiplier determines the value used in the clock module CLKCTRL[PLLMLTF] field. 3. F_{max} is determined by the maximum frequency of the peripheral and of the SC1400 core as specified in the data sheet. 							

3.4.3 Boot

After a power-on reset, the PLL is bypassed and the device is directly clocked from the CLKIN pin. Thus, the device operates slowly during the boot process. After the boot program is loaded, it can enable the PLL and start the device operating at a higher speed. The MSC7116 can boot from an external host through the HDI16 or download a user program through the I²C port. The boot operating mode is set by configuring the BM[0-3] signals sampled at the rising edge of PORESET, as shown in **Table 35**. See the *MSC711x Reference Manual* for details of boot program operation.

3.4.3.1 HDI16 Boot

If the MSC7116 device boots from an external host through the HDI16, the port is configured as follows:

- Operate in Non-DMA mode.
- Operate in polled mode on the device side.
- Operate in polled mode on the external host side.
- External host must write four 16-bit values at a time with the first word as the most significant and the fourth word as the least significant.

When booting from a power-on reset, the HDI16 is additionally configurable as follows:

- 8- or 16-bit mode as specified by the H8BIT pin.
- Data strobe as specified by the HDSP and HDDS pins.

These pins are sampled only on the deassertion of power-on reset. During a boot from a hard reset, the configuration of these pins is unaffected.

Note: When the HDI16 is used for booting or other purposes, bit 0 is the least significant bit and not the most significant bit as for other DSP products.

3.4.3.2 I²C Boot

When the MSC7116 device is configured to boot from the I²C port, the boot program configures the GPIO pins for I²C operation. Then the MSC7116 device initiates accesses to the I²C module, downloading data to the MSC7116 device. The I²C interface is configured as follows:

- PLL is disabled and bypassed so that the I²C module is clocked with the IPBus clock.
- I²C interface operates in master mode and polling is used.
- EPROM operates in slave mode.
- Clock divider is set to 128.
- Address of slave during boot is 0xA0.

The IPBus clock is internally divided to generate the bit clock, as follows:

- CLKIN must be a maximum of 100 MHz
- PLL is bypassed.
- IPBus clock = CLKIN/2 is a maximum of 50 MHz.
- I²C bit clock must be less than or equal to:
 - IPBus clock/I²C clock divider
 - 50 MHz (max)/128
 - 390.6 KHz

This satisfies the maximum clock rate requirement of 400 kbps for the I²C interface. For details on the boot procedure, see the “Boot Program” chapter of the *MSC711x Reference Manual*.

3.4.3.3 SPI Boot

When the MSC7116 device is configured to boot from the SPI port, the boot program configures the GPIO pins for SPI operation. Then the MSC7116 device initiates accesses to the SPI module, downloading data to the MSC7116 device. When the SPI routines run in the boot ROM, the MSC7116 is always configured as the SPI master. Booting through the SPI is supported for serial EEPROM devices and serial Flash devices. When a READ_ID instruction is issued to the serial memory device and the device returns a value of 0x00 or 0xFF, the routines for accessing a serial EEPROM are used, at a maximum frequency of 4 Mbps. Otherwise, the routines for accessing a serial Flash are used, and they can run at faster speeds. Booting is performed through one of two sets of pins:

- Main set: BM[2–3], HA3, and HCS2, which allow use of the PLL.
- Alternate set: UTXD, URXD, SDA, and SCL, which cannot be used with the PLL.

In either configuration, an error during SPI boot is flagged on the EVNT3 pin. For details on the boot procedure, see the “Boot Program” chapter of the *MSC711x Reference Manual*.

5 Package Information

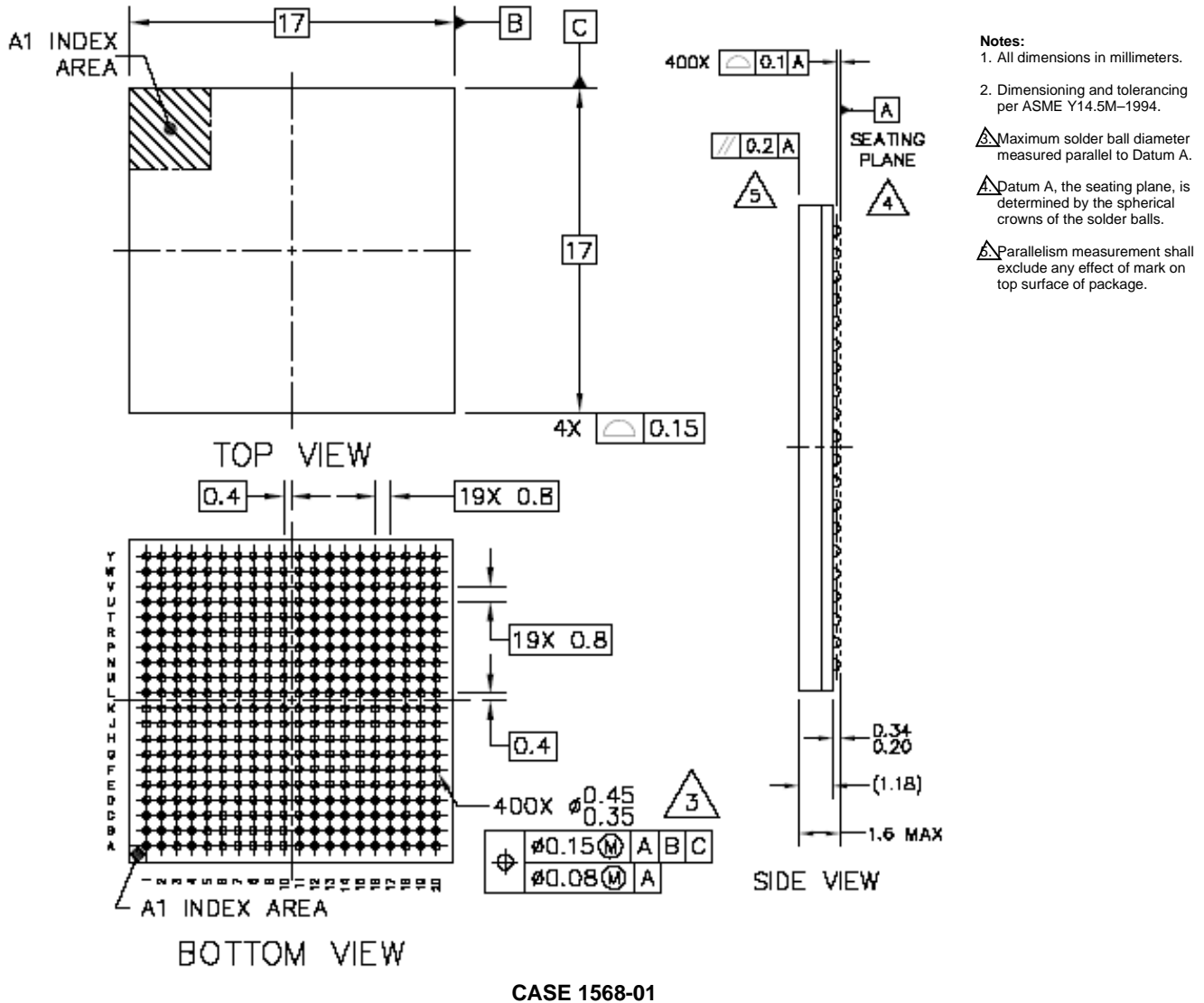


Figure 38. MSC7116 Mechanical Information, 400-pin MAP-BGA Package

6 Product Documentation

- *MSC711x Reference Manual* (MSC711xRM). Includes functional descriptions of the extended cores and all the internal subsystems including configuration and programming information.
- *Application Notes*. Cover various programming topics related to the StarCore DSP core and the MSC7116 device.
- *SC140/SC1400 DSP Core Reference Manual*. Covers the SC140 and SC1400 core architecture, control registers, clock registers, program control, and instruction set.

7 Revision History

Table 36 provides a revision history for this data sheet.

Table 36. Document Revision History

Revision	Date	Description
0	Apr 2004	<ul style="list-style-type: none"> Initial public release.
1	May 2004	<ul style="list-style-type: none"> Added ordering information and new package options.
2	Aug. 2004	<ul style="list-style-type: none"> Updated clock parameter values. Updated DDR timing specifications. Updated I²C timing specifications.
3	Sep. 2004	<ul style="list-style-type: none"> Updated Figures 1-2 and 1-2 to correct HDSP and DBREQ. Corrected EE0 port reference. Updated ball location for HDSP.
4	Jan. 2005	<ul style="list-style-type: none"> Added signal HA3. Updated absolute maximum ratings, DDR DRAM capacitance specifications, clock parameters, reset timing, and TDM timing. Added note for timing reference for I²C interface. Expanded GPIO timing information. Corrected pin T20 and K20 signal designation. Corrected signal names to GPA015 and $\overline{IRQ2}$. Expanded design guidelines in Chapter 4.
5	Mar. 2005	<ul style="list-style-type: none"> Updated features list. Updated power specifications. Changed CLKIN frequency range. Added clock configuration information. Updated JTAG timings.
6	Apr. 2005	<ul style="list-style-type: none"> Added recommended power supply ratings and updated equations to estimate power consumption.
7	Oct. 2005	<ul style="list-style-type: none"> Updated core and total power consumption examples.
8	Dec. 2005	<ul style="list-style-type: none"> Added information about the new mask set 1M88B. Affected all sections.
9	Nov. 2006	<ul style="list-style-type: none"> Updated arrows in Host DMA Writing Timing figure. Updated boot overview in Section 4.4.3.
10	Apr. 2007	<ul style="list-style-type: none"> Removed erroneous references to V_{CCSYN} and V_{CCSYN1}.
11	Jul. 2007	<ul style="list-style-type: none"> Updated to new data sheet format. Reorganized and renumbered sections, figures, and tables. Removed all references to obsolete mask set 1L44X and corresponding specification values. Added a note to clarify the definition of TCK timing 700 in new Table 31. Reworked reset and boot sections. Expanded I²C boot information and added SPI boot information. Removed obsolete part numbers.
12	Aug 2007	<ul style="list-style-type: none"> The power-up and power-down sequences described in Section 3.2 starting on page 42 have been expanded to five possible design scenarios/cases. These cases replace the previously recommended power-up/power-down sequence recommendations. Section 3.2 has been clarified by adding subsection headings.
13	Apr 2008	<ul style="list-style-type: none"> Change the PLL filter resistor from 20 Ω to 2 Ω in Section 3.2.5.

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